

YG233C2,N2,D2 (8A)

(200V / 8A)

FAST RECOVERY DIODE

Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

Applications

- High speed switching

Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		200	V
Isolating voltage	V_{iso}	Terminals-to-Case, AC.1min	1500	V
Average output current	I_o	Square wave, duty=1/2, $T_c=95^{\circ}C$	8*	A
Surge current	I_{FSM}	Sine wave 10ms	30	A
Operating junction temperature	T_j		+150	$^{\circ}C$
Storage temperature	T_{stg}		-40 to +150	$^{\circ}C$

*Average forward current of centertap full wave connection

- Electrical characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

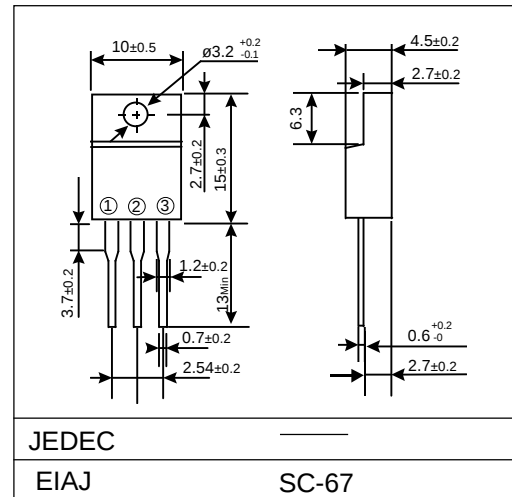
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop **	V_{FM}	$I_{FM}=2.0A$	1.4	V
Reverse current **	I_{RRM}	$V_R=V_{RRM}$	500	μA
Reverse recovery time	t_{rr}	$I_F=0.1A, I_R=0.1A$	0.1	μs
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5	$^{\circ}C/W$

** Rating per element

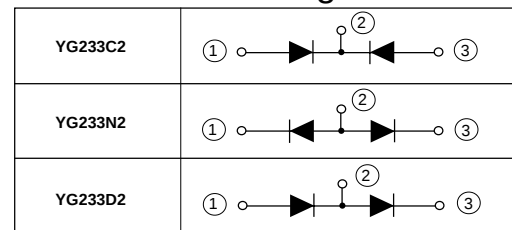
- Mechanical characteristics

Mounting torque	Recommended torque	0.3 to 0.5	N·m
Approximate weight		2.3	g

Outline drawings, mm

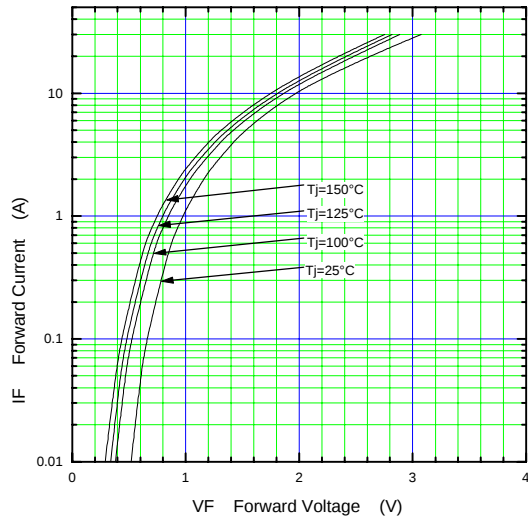


Connection diagram

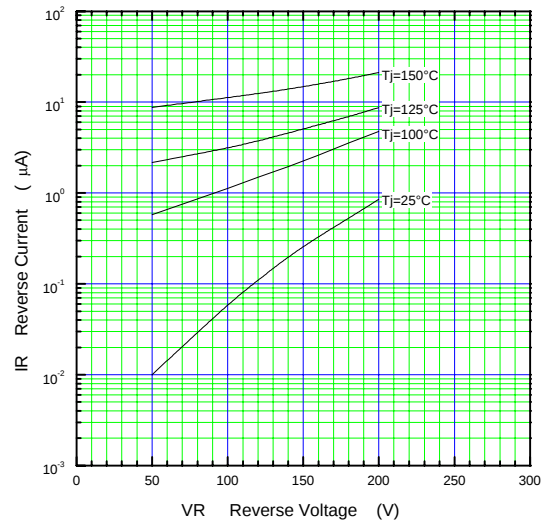


Characteristics

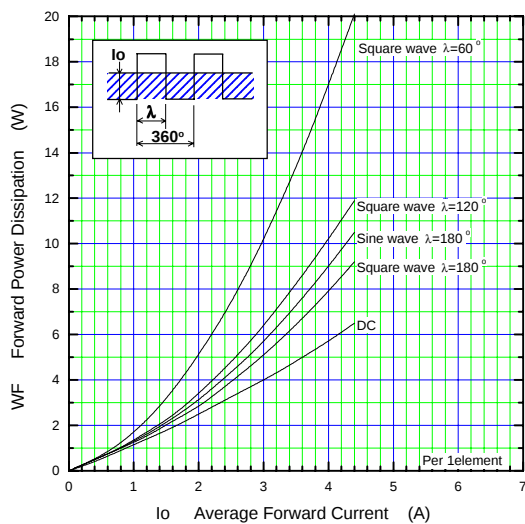
Forward Characteristic (typ.)



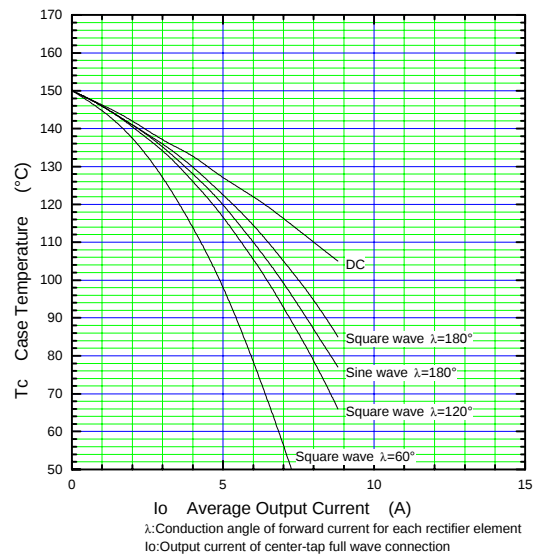
Reverse Characteristic (typ.)



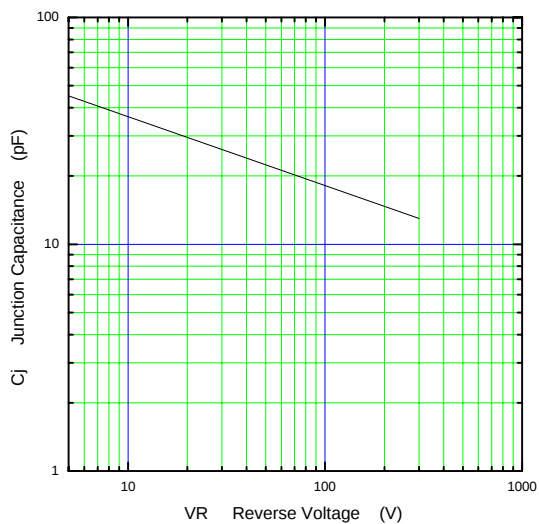
Forward Power Dissipation



Current Derating (I_o - T_c)



Junction Capacitance Characteristic (typ.)



Surge Capability

